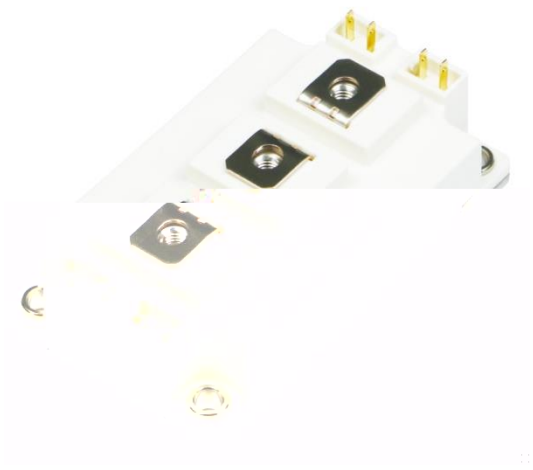
MG200HF12LEC2

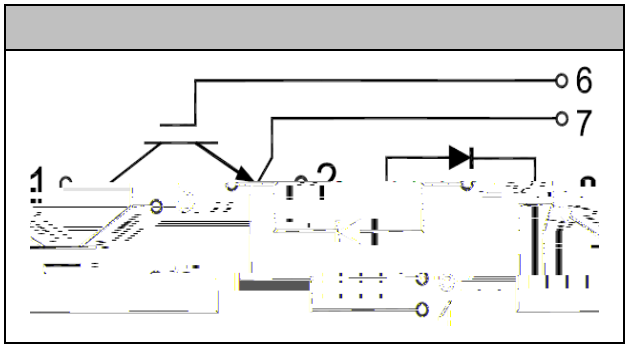


IGBT Modules

V_{CES} 1200V
I_C 200A

Applications

- High frequency drivers
- Solar inverters
- UPS (Uninterruptible Power Supplies)
- Electric welding machine



Features

- High speed IGBT in NPT technology
- Low switching losses
- High short circuit capability(10us)
- Including ultra fast & soft recovery anti-parallel FWD
- Low inductance
- Maximum junction temperature 150

● IGBT

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	V_{GE}=0V, I_C =1mA, T_{vj}=25℃	1200	V
Continuous Collector Current	I_C	T_c=80℃	200	A
Repetitive Peak Collector Current	I_{CRM}	tp=1ms	400	A
Gate-Emitter Voltage	V_{GES}	T_{vj}=25℃	±20	V
Total Power Dissipation	P_{tot}	T_c=25℃ T_{vjmax}=150℃	1358	W

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}$, I_C =8mA,T_{vj}=25℃	5.0	5.8	6.5	V
Collector-Emitter Cut-off Current	I_{CES}	V_{CE}=1200V,V_{GE}=0V,T_{vj}=25			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	Ic=200A,V_{GE}=15V, T_{vj}=25℃		3.0	3.5	V
		Ic=200A,V_{GE}=15V, T_{vj}=125℃		3.8		
Gate Charge	Q_G			2.0		uC
Input Capacitance	C_{ies}	V_{CE}=25V,V_{GE} =0V, f=1MHz,T_{vj}=25		13.2		nF
Reverse Transfer Capacitance	C_{res}			0.8		nF
Gate-Emitter leakage current	I_{GES}	V_{CE}=0 V, V_{GE}=20V,T_{vj} = 25℃			400	nA
Turn-on Delay Time	$t_{d(on)}$	I_C =200 A V_{CE} = 600 V V_{GE} = ± 15V R_{GON} = 5.1Ω R_{GOFF} =2.5Ω T_{vj}=25℃		105		ns
Rise Time	t_r			80		ns
Turn-off Delay Time	$t_{d(off)}$			285		ns
Fall Time	t_f			24		ns
Energy Dissipation During Turn-on Time	E_{on}			21.8		mJ
Energy Dissipation During Turn-off Time	E_{off}			7.0		mJ
Turn-on Delay Time	$t_{d(on)}$	I_C =200 A V_{CE} = 600 V V_{GE} = ± 15V R_{GON} = 5.1Ω R_{GOFF} =2.5Ω T_{vj}=125℃		112		ns
Rise Time	t_r			86		ns
Turn-off Delay Time	$t_{d(off)}$			330		ns
Fall Time	t_f			29		ns
Energy Dissipation During Turn-on Time	E_{on}			31.4		mJ
Energy Dissipation During Turn-off Time	E_{off}			10.2		mJ
SC Data	I_{sc}	T_p≤10us,V_{GE}=15V, Tvj=125℃,V_{cc}=600V, V_{CEM}≤1200V		1500		A

Diode

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	T_{vj}=25℃	1200	V
Continuous DC Forward Current	I_F		200	A
Repetitive Peak Forward Current	I_{FRM}	t_p=1ms	400	A

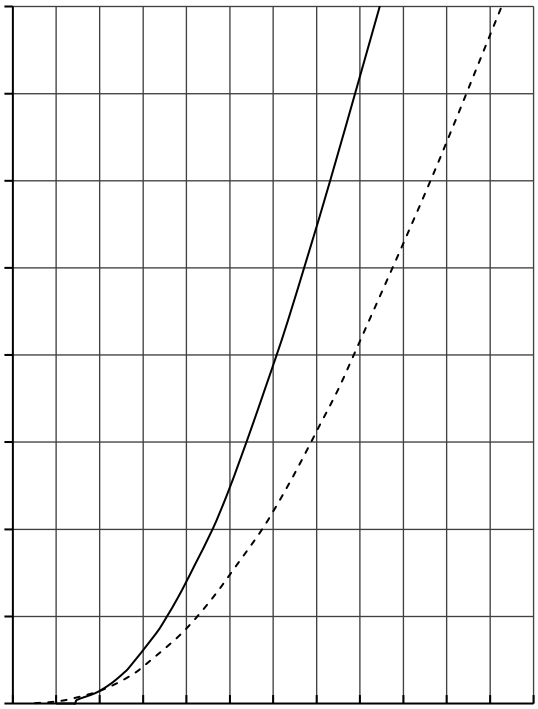
Characteristic values

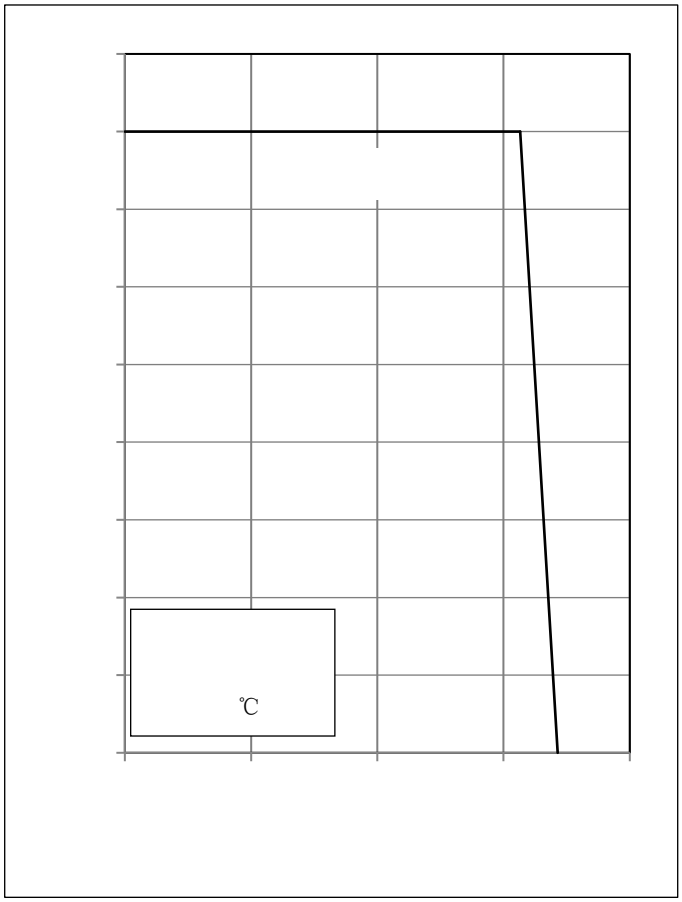
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	I_F=200A,T_{vj}=25℃		1.90	2.3	V
		I_F=200A,T_{vj}=125℃		1.95		
Recovered Charge	Q_{rr}	I_F =200 A V_R=600V -di_F/dt =2500A/us T_{vj}=25℃		11.5		uC
Peak Reverse Recovery Current	I_{rr}			105		A
Reverse Recovery Energy	E_{rec}			6.8		mJ
Recovered Charge	Q_{rr}	I_F =200 A V_R=600V -di_F/dt =2500A/us T_{vj}=125℃		20.8		uC
Peak Reverse Recovery Current	I_{rr}			124		A
Reverse Recovery Energy	E_{rec}			13.8		mJ

Module Characteristics T_C=25°C unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation voltage	V_{isol}	t=1min,f=50Hz	2500			V
Maximum Junction Temperature	T_{jmax}				150	℃
Operating Junction Temperature	$T_{vj\ op}$		-40		125	℃
Storage Temperature	T_{stg}		-40		125	℃
Thermal Resistance Junction-to Case	$R_{\theta JC}$	per IGBT			0.09	K/W
		per Diode			0.19	

KW

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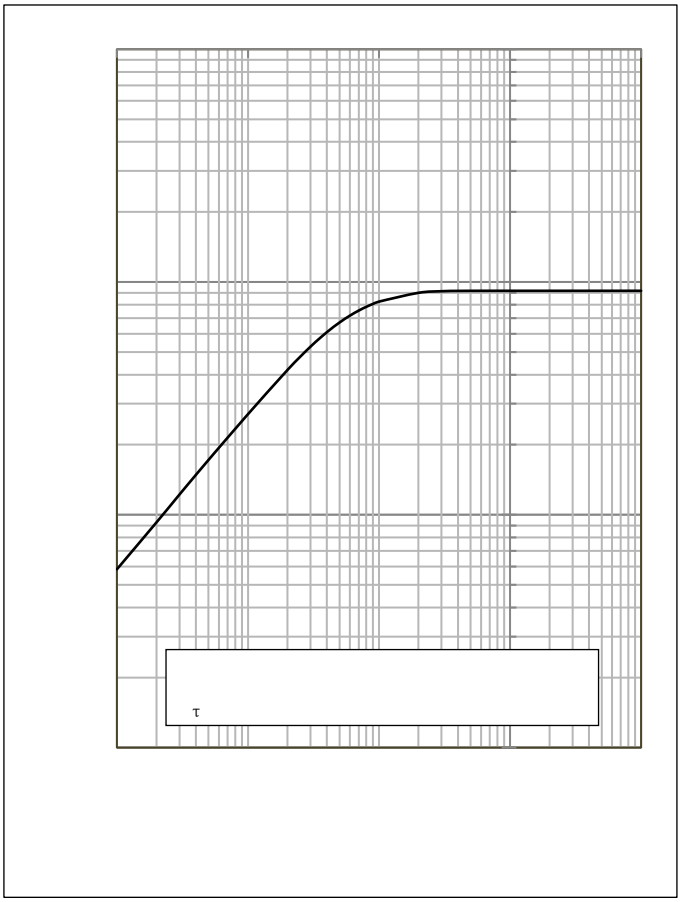
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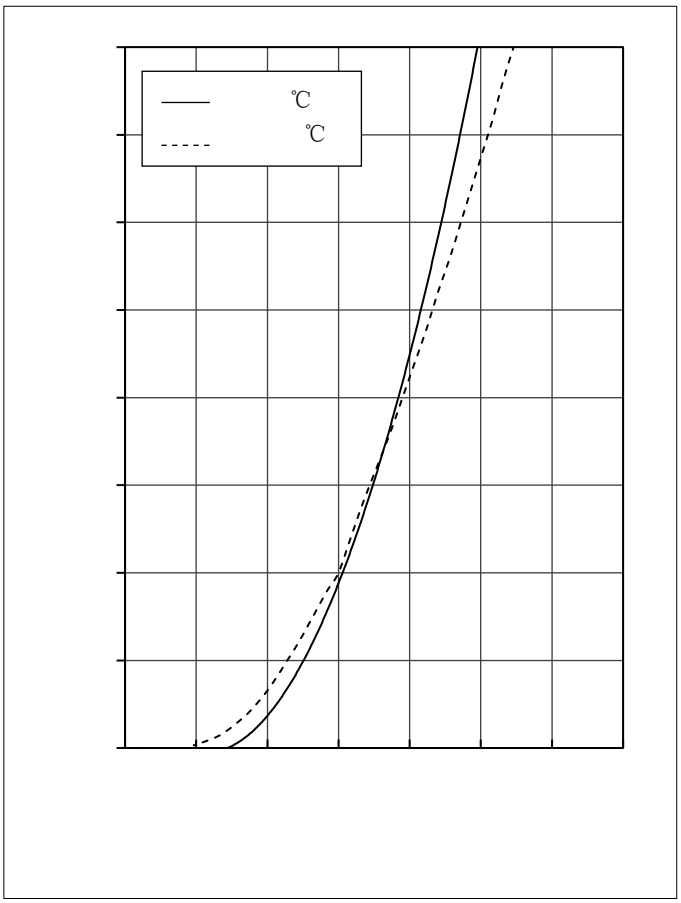
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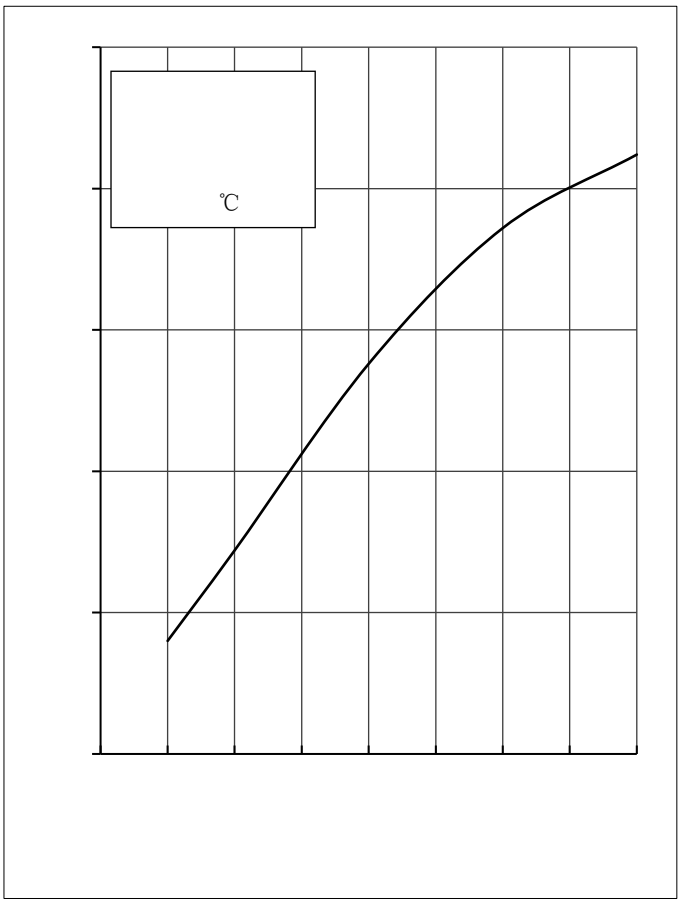
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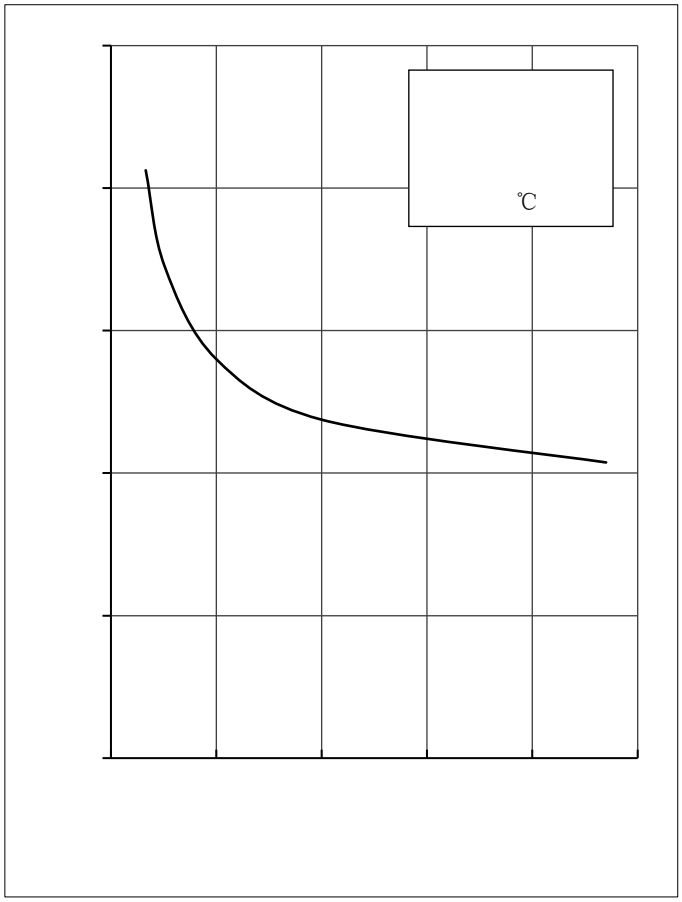
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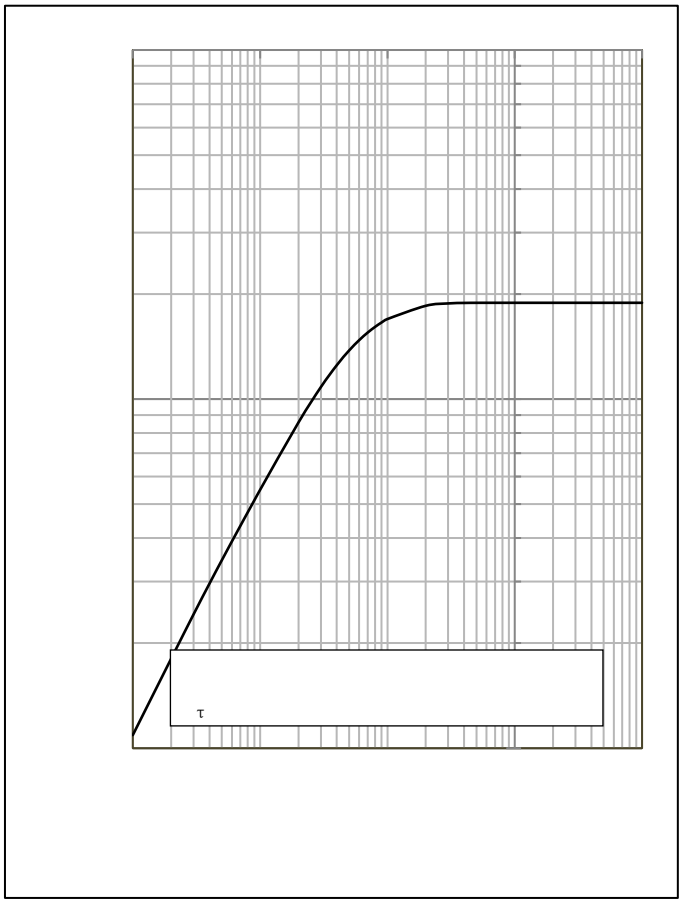
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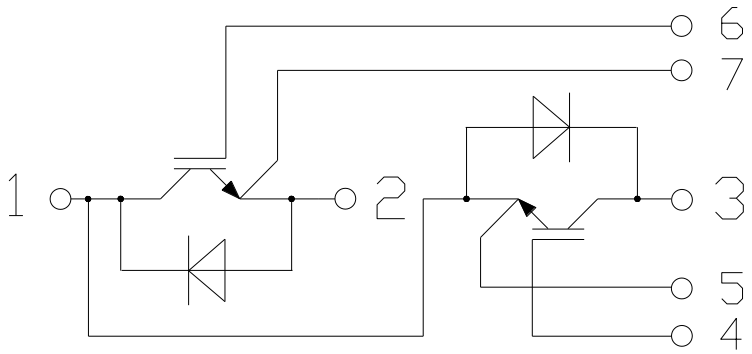
- **Circuit Diagram**



- **Package Outline Information**

Dimensions in Millimeters